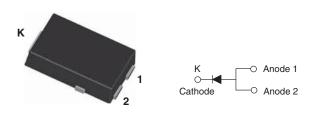
### **Vishay Semiconductors**

# Hyper Fast Rectifier, 6 A FRED Pt<sup>®</sup>



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SMPC (TO-277A)

PRODUCT SUMMARY							
Package	SMPC (TO-277A)						
I <sub>F(AV)</sub>	6 A						
V <sub>R</sub>	600 V						
V <sub>F</sub> at I <sub>F</sub>	1.05 V						
t <sub>rr (typ.)</sub>	33 ns						
T <sub>J</sub> max.	175 °C						
Diode variation	Single die						

#### **FEATURES**

- Hyper fast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- For PFC, CRM/CCM, snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

State of the art hyper fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, lighting, in the AC/DC section of SMPS, freewheeling and clamp diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	V <sub>RRM</sub>		600	V				
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>Sp</sub> = 145 °C	6	А				
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	90	A				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C				

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 6 A	-	1.30	1.80	V		
Forward voltage		I <sub>F</sub> = 6 A, T <sub>J</sub> = 150 °C	-	1.05	1.55			
	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	5			
Reverse leakage current		$T_J = 150 \ ^{\circ}C, V_R = V_R \text{ rated}$	-	50	300	μA		
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	8	-	pF		

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, \ dI_F/dt = 50 \text{ A}$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		33	-			
Povereo recover timo	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	40			
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	40	-	A nC		
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 6 A dI <sub>F</sub> /dt = 500 A/µs V <sub>R</sub> = 400 V	-	75	-			
Deals receivers ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	6.8	-			
Peak recovery current		T <sub>J</sub> = 125 °C		-	11	-			
	0	T <sub>J</sub> = 25 °C		-	140	-			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	400	-			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS MIN. TYP. MAX.							
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C			
Thermal resistance, junction to solder pad	R <sub>thJ-Sp</sub>		-	2.4	3.5	°C/W			
Approximate weight				0.1		g			
Approximate weight				0.0035		oz.			
Marking device		Case style SMPC (TO-277A)		NE	H6				

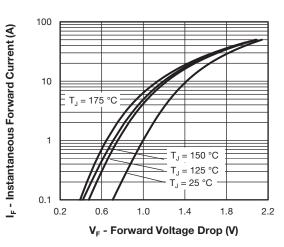


Fig. 1 - Typical Forward Voltage Drop Characteristics

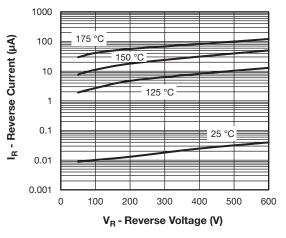
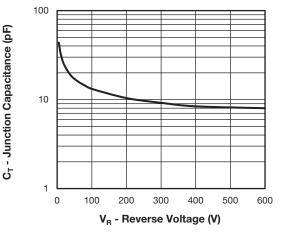


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

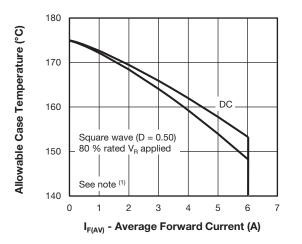
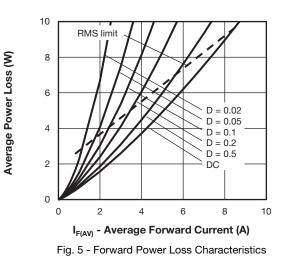


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current



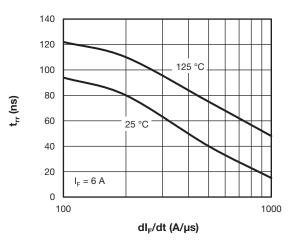


Fig. 6 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

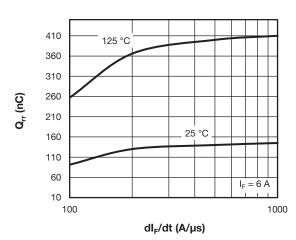


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

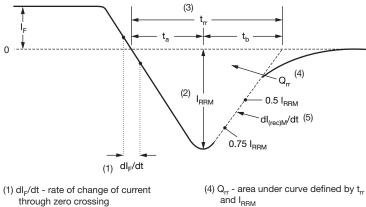
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## **VS-6ESH06-M3**

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- (2)  $I_{\text{RRM}}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75  $I_{\text{RRM}}$  and 0.50  $I_{\text{RRM}}$  extrapolated to zero current.

and I<sub>RRM</sub>

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

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Device co

de	VS-		6	Е	S	н	06	-M3		
	1	. (	2	3	4	5	6	7		
	1	-	Visł	nay Sem	niconduc	ctors pro	oduct			
	2	-	Cur	Current rating (6 = 6 A)						
	3	-	Circ	Circuit configuration:						
			E =	E = single diode						
	4	-	S =	S = SMPC package						
	5	-	Pro	Process type,						
			H =	H = hyper fast recovery						
	6	-	Volt	Voltage code (06 = 600 V)						
	7	-	-M3	-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-						

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-6ESH06-M3/86A	1500	1500	7" diameter plastic tape and reel				
VS-6ESH06-M3/87A	6500	6500	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95570				
Part marking information	www.vishay.com/doc?95565				
Packaging information	www.vishay.com/doc?88869				

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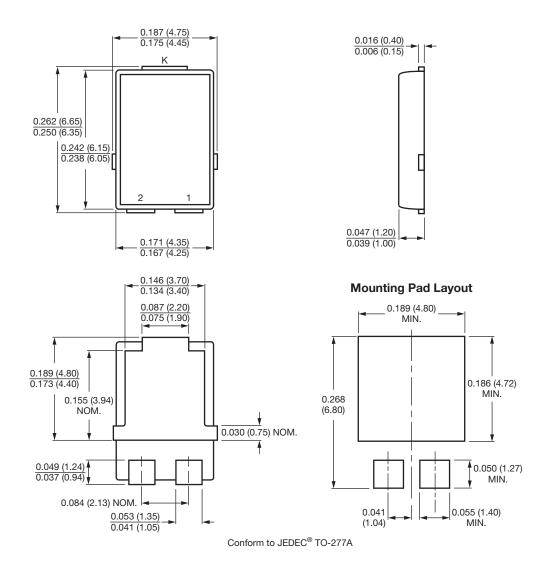
## **Outline Dimensions**





TO-277A (SMPC)

#### **DIMENSIONS** in inches (millimeters)





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